

Advance Information
The RF Small Signal Line
Silicon Lateral FET
N-Channel Enhancement-Mode MOSFET

MRF9745T1

30 dBm, 900 MHz
HIGH FREQUENCY
POWER TRANSISTOR
LD MOS FET

Designed for use in low voltage, moderate power amplifiers such as portable analog and digital cellular radios and PC RF modems.

- Performance Specifications at 5.8 V, 900 MHz:
Output Power = 30 dBm Min
Power Gain = 10 dB Typ
Efficiency = 50% Min
- Guaranteed Ruggedness at Load VSWR = 20:1
- New Plastic Surface Mount Package
- Available in Tape and Reel Packaging.
T1 Suffix = 1,000 Units per 8 mm, 7 inch Reel
- Device Marking = 9745



CASE 449-02, STYLE 1
(PLD-1)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	35	Vdc
Drain-Gate Voltage ($R_{GS} = 1 M\Omega$)	V_{DGO}	25	Vdc
Gate-Source Voltage	V_{GS}	± 10	Vdc
Drain Current - Continuous	I_D	2	Adc
Total Device Dissipation @ $T_C = 50^\circ C$ Derate above $50^\circ C$	P_D	10 100	W mW/ $^\circ C$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ C$
Operating Temperature Range	T_J	150	$^\circ C$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	10	$^\circ C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Leakage Current ($V_{DS} = 35 V, V_{GS} = 0$)	I_{DSS}	-	-	10	μA_{dc}
Gate-Source Leakage Current ($V_{GS} = 5 V, V_{DS} = 0$)	I_{GSS}	-	-	1	μA_{dc}

NOTE - **CAUTION** - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

ELECTRICAL CHARACTERISTICS – continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
Gate Threshold Voltage ($V_{DS} = 6\text{ V}$, $I_D = 25\ \mu\text{A}$)	$V_{GS(th)}$	1	2	3	Vdc
Forward Transconductance ($V_{DS} = 6\text{ V}$, $I_D = 200\text{ mA}$)	g_{fs}	–	550	–	mmhos
Resistance Drain–Source ($V_{GS} = 4\text{ V}$, $I_D = 100\text{ mA}$)	$R_{DS(on)}$	–	1	2.5	Ω

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 6\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{iss}	–	14	–	pF
Output Capacitance ($V_{DS} = 6\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{oss}	–	11	–	pF
Feedback Capacitance ($V_{DS} = 6\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	–	1.8	–	pF

FUNCTIONAL CHARACTERISTICS

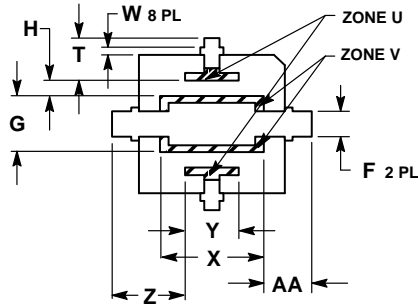
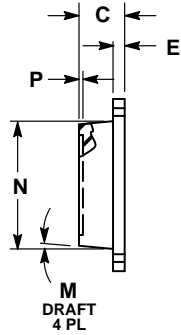
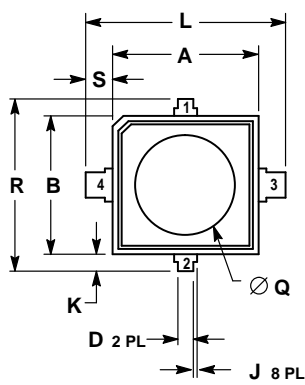
Power Gain ($V_{DD} = 5.8\text{ Vdc}$, $P_{in} = 20\text{ dBm}$, $I_{DQ} = 150\text{ mA}$, $f = 900\text{ MHz}$)	G_{ps}	9.5	10	–	dB
Drain Efficiency ($V_{DD} = 5.8\text{ Vdc}$, $P_{in} = 20\text{ dBm}$, $I_{DQ} = 150\text{ mA}$, $f = 900\text{ MHz}$)	η_D	50	55	–	%
Ruggedness Test ($V_{DD} = 5.8\text{ Vdc}$, $P_{in} = 20\text{ dBm}$, $I_{DQ} = 150\text{ mA}$, $f = 900\text{ MHz}$, Load VSWR = 20:1, All Phase Angles at Frequency Test)	Ψ	No Degradation in Output Power after Test			

Table 1. Large Signal Impedance
 $V_{DD} = 5.8\text{ V}$, $P_{in} = 20\text{ dBm}$, $I_{DQ} = 150\text{ mA}$

f MHz	Z_{in} Ohms	Z_{OL}^* Ohms
850	7.0 – j6.4	6.1 – j5.1
900	5.2 – j6.5	5.9 – j4.6
950	5.2 – j6.0	6.1 – j4.7

Z_{OL}^* is the conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

PACKAGE DIMENSIONS




RESIN BLEED/FLASH ALLOWABLE

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.195	4.70	4.95
B	0.175	0.185	4.44	4.70
C	0.058	0.064	1.47	1.63
D	0.017	0.023	0.43	0.58
E	0.014	0.017	0.36	0.43
F	0.027	0.033	0.69	0.84
G	0.071	0.077	1.80	1.96
H	0.017	0.023	0.43	0.58
J	0.000	0.007	0.00	0.18
K	0.018	0.026	0.46	0.66
L	0.253	0.263	6.43	6.68
M	5°REF		5°REF	
N	1.75 REF		4.44 REF	
P	0.000	0.006	0.00	0.15
Q	0.120	0.130	3.05	3.30
R	0.220	0.230	5.59	5.84
S	0.030	0.038	0.76	0.97
T	0.050	0.060	1.27	1.52
U	0.000	0.018	0.00	0.46
V	0.000	0.014	0.00	0.36
W	0.004	0.016	0.10	0.41
X	0.131	0.141	3.33	3.58
Y	0.065	0.075	1.65	1.90
Z	0.089	0.099	2.26	2.51
AA	0.056	0.066	1.42	1.67

**CASE 449-02
 ISSUE A**

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE
 4. SOURCE

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